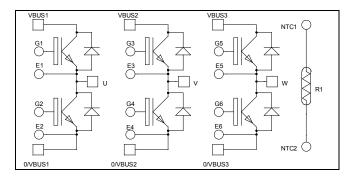


Triple phase leg Trench + Field Stop IGBT4 Power module





VBUS2

® G3 **®** E3 VBUS3

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT 4 Technology
 - Low voltage drop
 - Low leakage current
 - Low switching losses
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
 - Symmetrical design
- Kelvin emitter for easy drive
 - Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
 - High level of integration
- Internal thermistor for temperature monitoring



- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

VBUS1

NTC2

_® G1 ® E1

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
Ţ	Continuous Colloctor Current	$T_c = 25$ °C	140	
I_{C}	Continuous Collector Current	$T_c = 80^{\circ}C$	120	Α
I_{CM}	Pulsed Collector Current	$T_c = 25^{\circ}C$	200	
V_{GE}	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_c = 25$ °C	517	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^{\circ}C$	200A @ 1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				250	μA
V	Collector Emitter saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		1.8	2.15	V
$V_{CE(sat)}$		$I_C = 100A$ $T_j = 150^{\circ}C$		2.15		·	
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$, $I_C =$	3.4mA	5.2	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				600	nA

Dynamic Characteristics

·	Characteristic	Test Conditions	ī.	Min	Typ	Max	Unit	
Cies	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$			6.2			
C_{oes}	Output Capacitance				0.4		nF	
C_{res}	Reverse Transfer Capacitance				0.35			
Q_{G}	Gate charge	$V_{GE} = \pm 15V ; V_{CE} = 600V$ $I_{C} = 100A$			0.85		μС	
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching (25°C)		130			
T_{r}	Rise Time	$V_{GE} = \pm 15V$			20			
$T_{d(off)}$	Turn-off Delay Time	$I_{\rm C} = 100 \text{A}$	$V_{Bus} = 600V$		300		ns	
$T_{\rm f}$	Fall Time	$R_G = 7.5\Omega$			45			
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (150°C) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$			150		ns	
$T_{\rm r}$	Rise Time				35			
$T_{d(off)}$	Turn-off Delay Time	$I_C = 100A$			350			
$T_{\rm f}$	Fall Time	$R_G = 7.5\Omega$			80			
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V$	$T_J = 25^{\circ}C$		5		mI	
Lon	Turn-on Switching Energy	$V_{\text{Bus}} = 600 \text{V}$	$V_{\text{Bus}} = 600 \text{V}$ T_{J}	$V_{Bus} = 600V$ $T_{J} = 150^{\circ}C$		10.5		mJ
E_{off}	I _C = 10	$I_{\rm C} = 100 {\rm A}$	$T_J = 25^{\circ}C$		5.5		mJ	
Loff	Turn-off Switching Energy	$R_G = 7.5\Omega$	$R_{\rm G} = 7.5\Omega \qquad T_{\rm J} = 150^{\circ} \rm C$	$T_{\rm J} = 150^{\circ}{\rm C}$		9.5		1113
I_{sc}	Short Circuit data	$V_{GE} \le 15V ; V_{Bu}$ $t_p \le 10 \mu s ; T_j = 1$			400		A	

Chopper diode ratings and characteristics

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Symbol	Characteristic	Test Conditions	Test Conditions		Typ	Max	Unit	
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V	
I_{RM}	Maximum Reverse Leakage Current	V _R =1200V	$T_j = 25$ °C			250	μΑ	
I_F	DC Forward Current		$Tc = 80^{\circ}C$		120		A	
V	Diode Forward Voltage	$I_F = 100A$	$T_i = 25^{\circ}C$		1.9	2.4	V	
V_{F}		$V_{GE} = 0V$	$T_{i} = 150^{\circ}C$		1.85		V	
4	Reverse Recovery Time	$T_i = 150^{\circ}C$	$T_j = 25$ °C		155			
t_{rr}			$T_{j} = 150^{\circ}C$		300		ns	
0	Daniera Baranam Chama	$ \begin{array}{c} I_F = 100A \\ V_R = 600V \\ di/dt = 2400A/\mu s \end{array} $	$T_j = 25$ °C		9.3		C	
Q_{rr}	Reverse Recovery Charge		$T_{j} = 150^{\circ}C$		20		μC	
E_{rr}	Reverse Recovery Energy	$T_j = 25$	$T_j = 25$ °C		3.4		mJ	
			$T_i = 150^{\circ}C$		8		1113	



Thermal and package characteristics

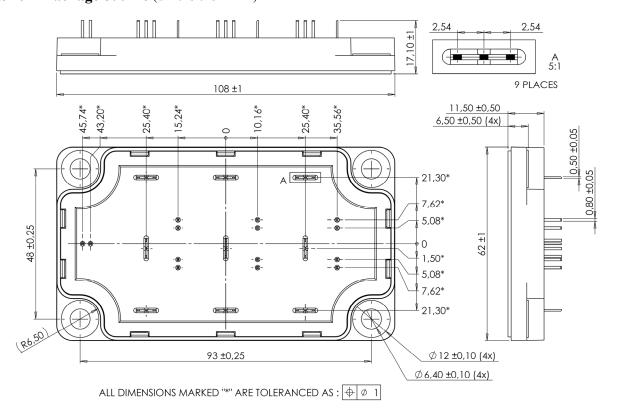
Symbol	Characteristic			Min	Тур	Max	Unit
D	Junction to Case Thermal Resistance		IGBT			0.29	°C/W
R_{thJC}			Diode			0.5	C/W
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V
T_{J}	Operating junction temperature range			-40		175	
T_{STG}	Storage Temperature Range		-40		125	°C	
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
Wt	Package Weight				250	g	

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol	Characteristic		Min	Typ	Max	Unit
R ₂₅	Resistance @ 25°C	sistance @ 25°C		50		kΩ
$\Delta R_{25}/R_{25}$				5		%
$B_{25/85}$	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta \mathrm{B/B}$		T _C =100°C		4		%

$$R_{T} = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]} \quad \text{T: Thermistor temperature} \\ R_{T}: \text{ Thermistor value at T}$$

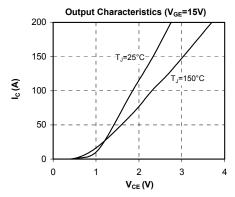
SP6-P Package outline (dimensions in mm)

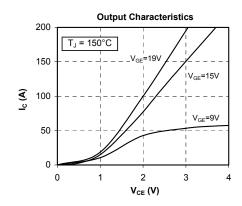


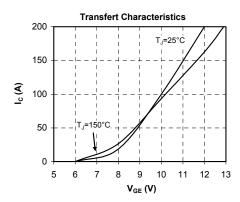
See application note 1902 - Mounting Instructions for SP6-P (12mm) Power Modules on www.microsemi.com

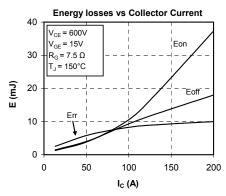


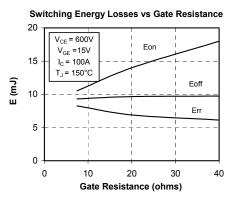
Typical Performance Curve

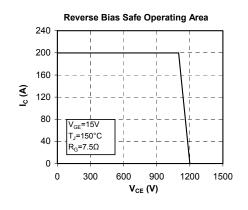


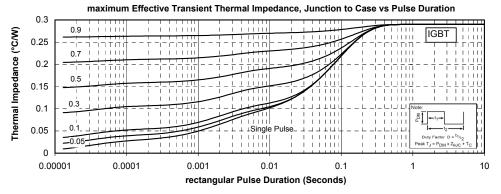




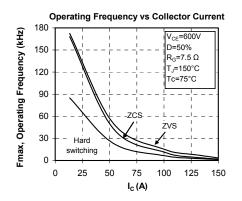


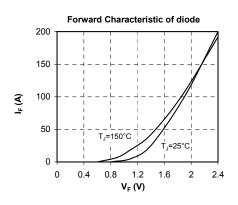


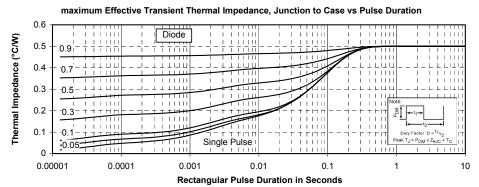












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